

1N6263WS

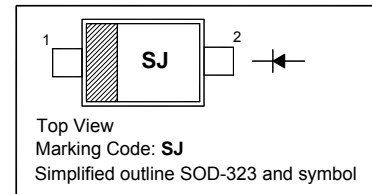
Surface Mount Schottky Barrier Diodes

Features

- Low forward voltage
- Low reverse capacitance

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

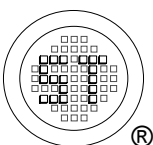


Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	60	V
Reverse Voltage	V_R	60	V
Forward Continuous Current	I_{FM}	15	mA
Power Dissipation	P_d	200	mW
Non-Repetitive Peak Forward Surge Current	I_{FSM}	50 2	mA A
		at $t = 1\text{ s}$ at $t = 10\text{ }\mu\text{s}$	
Operating and Storage Temperature Range	T_j, T_{stg}	- 65 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 10\text{ }\mu\text{A}$	$V_{(BR)R}$	60	-	V
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 15\text{ mA}$	V_F	- -	0.41 1	V
Reverse Current at $V_R = 50\text{ V}$	I_R	-	200	nA
Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_T	-	2	pF
Reverse Recovery Time at $I_F = I_R = 5\text{ mA}$, $I_{rr} = 0.1 \times I_R$, $R_L = 100\text{ }\Omega$	t_{rr}	-	1	ns



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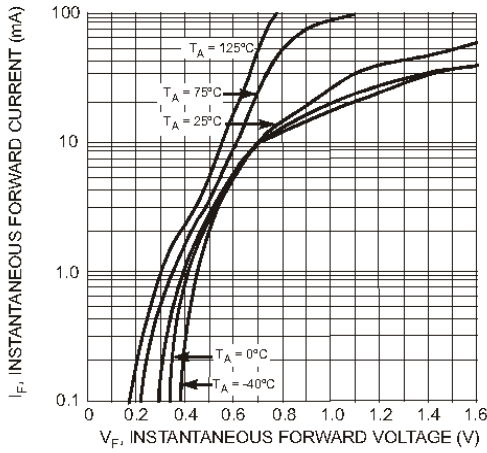


Fig. 1 Typical Forward Characteristics

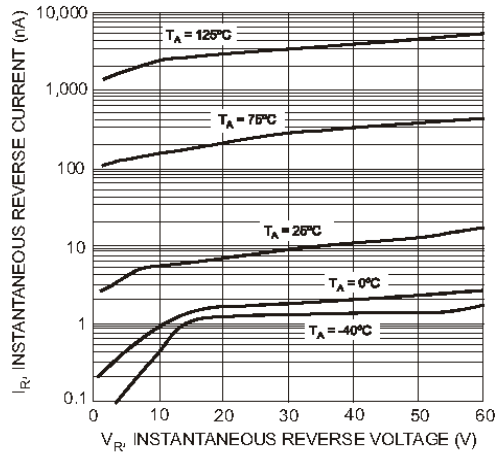


Fig. 2 Typical Reverse Characteristics

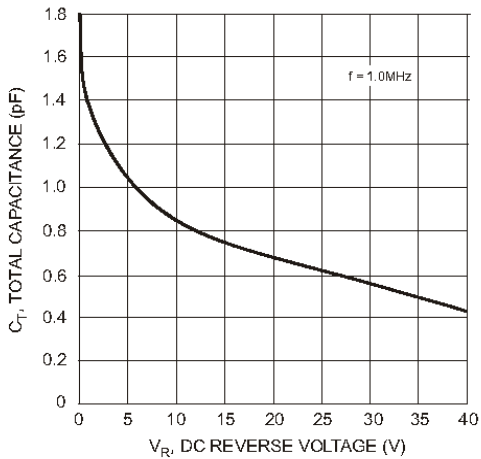


Fig. 3 Total Capacitance vs. Reverse Voltage

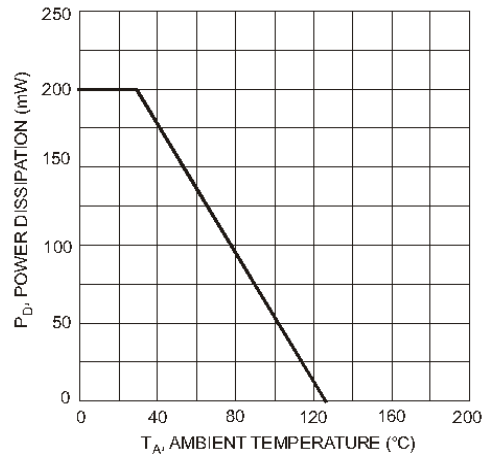
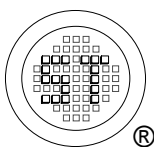


Fig. 4 Power Derating Curve



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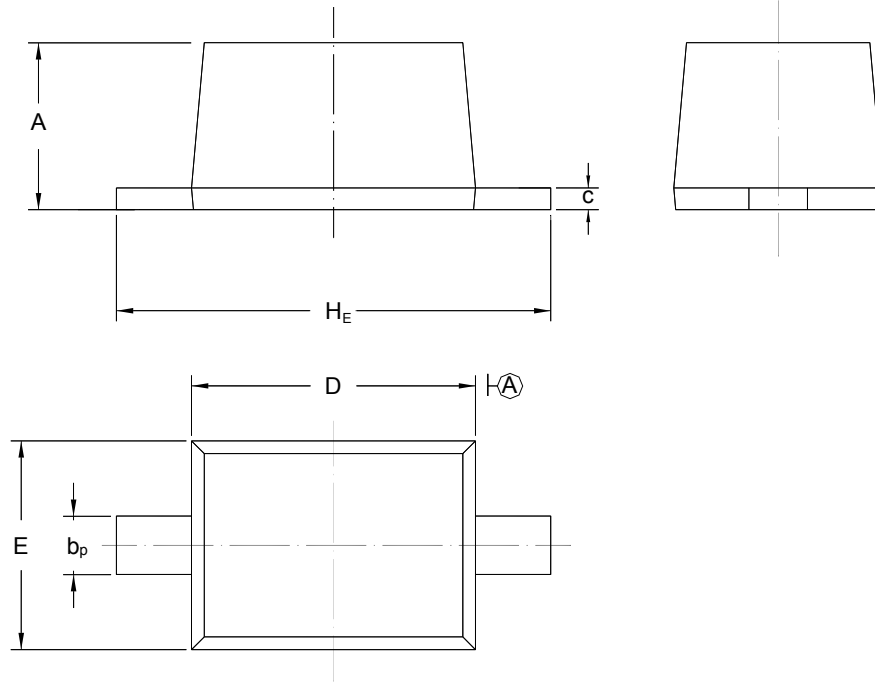


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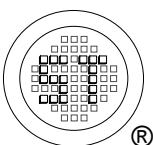
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



UNIT	A	b_p	C	D	E	H_E
mm	1.10 0.80	0.40 0.25	0.15 0.10	1.80 1.60	1.35 1.15	2.80 2.30



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